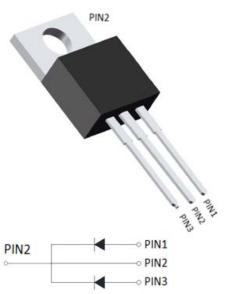
Ultra-Fast Recovery Rectifier Diodes



Features

- High frequency operation
- High surge forward current capability
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Adopt GPP chip
- Passivation for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

- Package: TO-220AB Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- Terminals: Tin plated leads, solderable per J-STD-002 and JESD22-B102
- Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MUR2010CT- B1-0000S	MUR2015CT- B1-0000S	MUR2020CT- B1-0000S	MUR2040CT-B1- 0000S	MUR2060CT- B1-0000S
Device Marking Code			MUR2010CT	MUR2015CT	MUR2020CT	MUR2040CT	MUR2060CT
Repetitive Peak Reverse Voltage	VRRM	V	100	150	200	400	600
Average Rectified Output Current @60Hz half sine-wave, R-load, Tc(FIG.1)	lo	А	20				
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25℃	IFSM	А	125				
Current Squared Time @1ms≤t≤8.3ms Tj=25℃, Rating of per diode	l²t	A²s	65				
Storage Temperature	Tstg	°C	-55 ~ +150				
Junction Temperature	Tj	°C	-55 ~ +150				

■Electrical Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MUR2010CT- B1-0000S	MUR2015CT- B1-0000S	MUR2020CT- B1-0000S	MUR2040CT- B1-0000S	MUR2060CT- B1-0000S
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=10.0A		0.975		1.3	1.5
Maximum DC reverse current at	IRRM1		VRM=VRRM T _a =25℃	10				
rated DC blocking voltage per diode	IRRM2	uA	VRM=VRRM T _a =125℃	500				
Reverse Recovery Time	Trr	ns	I _F =0.5A I _{RM} =1A I _{RR} =0.25A	50				

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

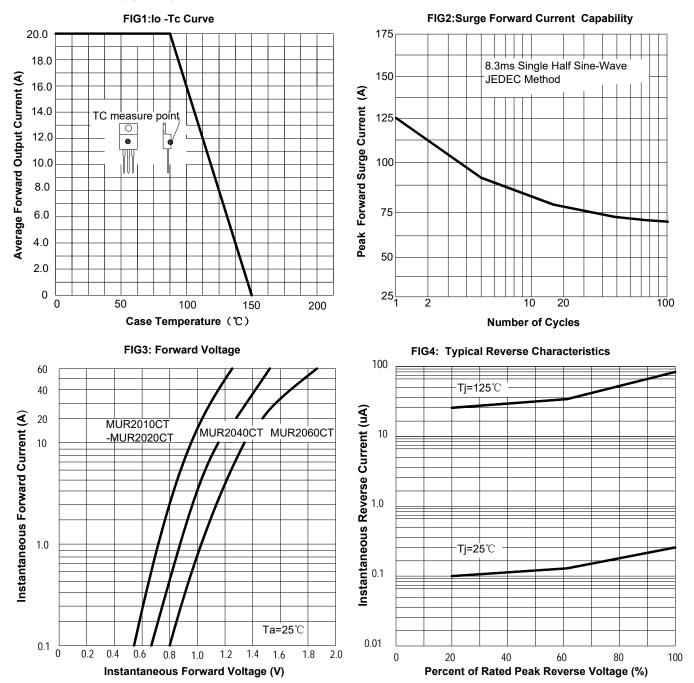
PAF	RAMETER	SYMBOL	UNIT	MUR2010CT- B1-0000S	MUR2015CT- B1-0000S	MUR2020CT- B1-0000S	MUR2040CT- B1-0000S	MUR2060CT- B1-00000S
Thermal Resistance	Between junction and case	$R_{_{ ext{ hetaJ-C}}}$	°C /W			2.0		

MUR2010CT THRU MUR2060CT-B1-0000S

Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MUR2010CT THRU MUR2060CT-B1-0000S	Approximate 1.90	50	1000	5000	Tube

■Characteristics (Typical)



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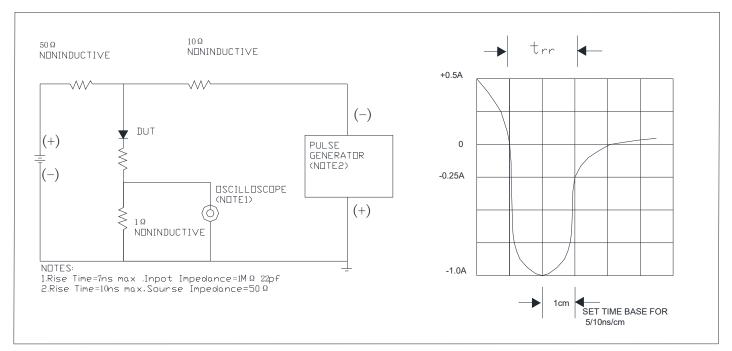
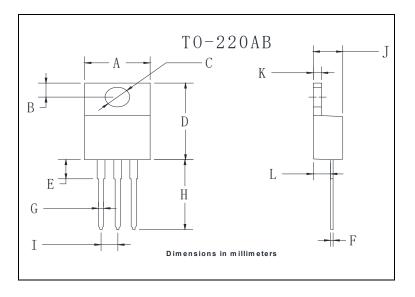


FIG.5 Diagram of circuit and Testing wave form of reverse recovery time

Outline Dimensions



TO-220AB					
Dim	Min	Max			
А	9.5	10.9			
В	2.22	3.27			
С	3.34	4.31			
D	14.5	15.5			
E	3.16	4.46			
F	0.28	0.64			
G	0.68	0.94			
Н	13.06	14.62			
I	2.01	3.07			
J	4.04	5.1			
К	1.14	1.4			
L	2.14	3.19			

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